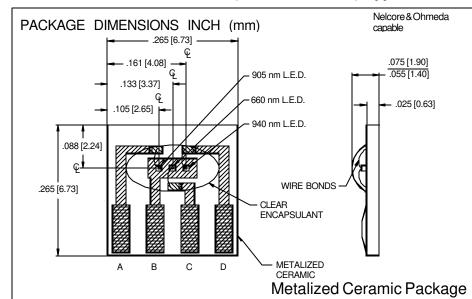
PHOTONIC DETECTORS INC.

Four Drive Emitter, Oximeter Component (905/660/940 nm) Type PDI-E840





FEATURES

- Low cost
- 660 nm +/- 3 nm
- 4 drive line

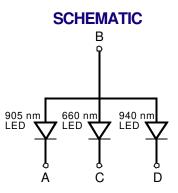
DESCRIPTION: The **PDI-E840** is a four drive line three emitter oximeter component. The 905, 660 GaAlAs and 940 nm GaAs emitters are high power LPE grown. The metalized ceramic has clear epoxy encapsulation with top side solder pads. These components are ideal for O.E.M. and repair replacements of oximeter probe assemblies.

APPLICATIONS

- Oximeter probes
- Finger clamps
- Reusable probes

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
Pd	Power Dissipation I _F =20 mA		250	mW	
ا _۳	Continuous Forward Current		30	mA	
FP	Peak Forward Current		200	mA	
V R	Reverse Voltage		4	V	
T₀&T₅	Storage & Operating Temp	-40	+80	۰C	
TS	Soldering Temperature*		240	°C	



*For3 seconds max using a heat sink.

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST	905 nm		660 nm		940 nm					
		COND	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Po	Radiant Flux**	l _F = 20 mA	1.2	1.8		1.8	2.4		1.2	1.8		mW
Ιv	Luminous Intensity**	I _F = 20 mA				20	30					mcd
VF	Forward Voltage	l _F = 20 mA		1.2	1.5		1.8	2.4		1.3	1.5	V
V _R	Reverse breakdown	I _F = 10 µuA	5			5			5			V
λ_{p}	Peak Wavelength	I _F = 20 mA	895	905	915	658	661	664	930	904	950	nm
Δλ	Spectral Bandwidth	I _F = 20 mA		50			25			50		nm
T _r	Rise Time	I _F = 20 mA		0.8			0.8			0.8		μS
Tr	Fall Time	l _F = 20 mA		0.8			0.8			0.8		μS

** Bare chip measured packaged in a flat TO-18/TO-46 header without resin coating.

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. [FORM NO. 100-PDI-E840 REV A]